



PRODUCT DATA SHEET



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Datasheet



Resources



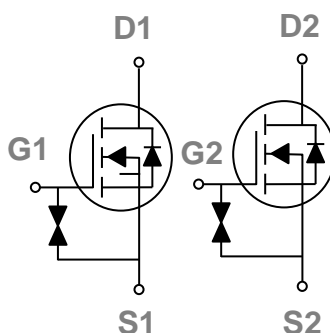
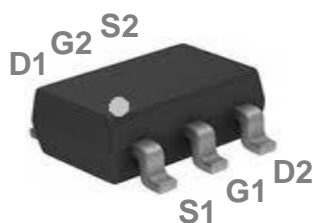
Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

SOT363



Features

- 30V, 0.3A, $R_{DS(ON)} = 1.1\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available
- G-S ESD Protection Diode Embedded
- ESD protected up to 2KV

Applications

- Motor Drive
- Power Tools
- LED Lighting

Absolute Maximum Ratings $T_c = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_A = 25^\circ\text{C}$)	0.3	A
	Drain Current – Continuous ($T_A = 70^\circ\text{C}$)	0.2	A
I_{DM}	Drain Current – Pulsed ¹	0.9	A
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$)	0.28	W
	Power Dissipation – Derate above 25°C	0.002	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-50 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-50 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	450	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.04	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±10	uA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =0.3A	---	1.1	1.5	Ω
		V _{GS} =4.5V, I _D =0.2A	---	1.3	2.2	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.8	1.1	1.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =0.1A	---	0.24	---	S

Dynamic and switching Characteristics

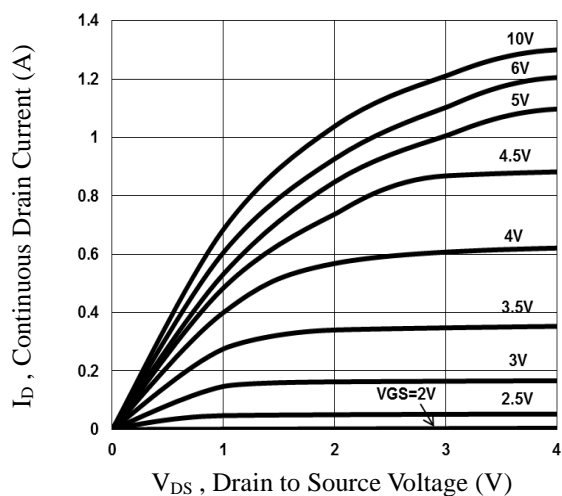
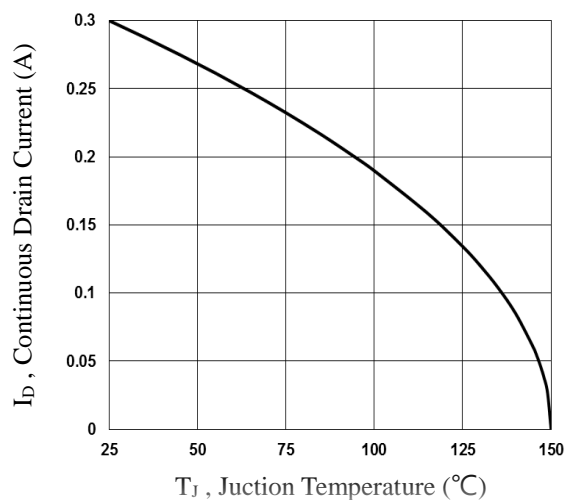
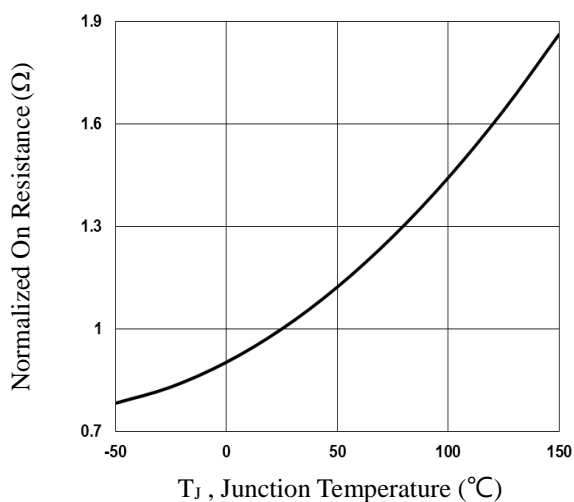
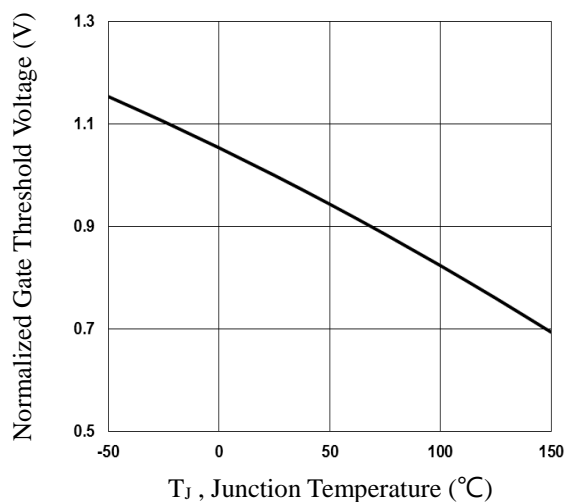
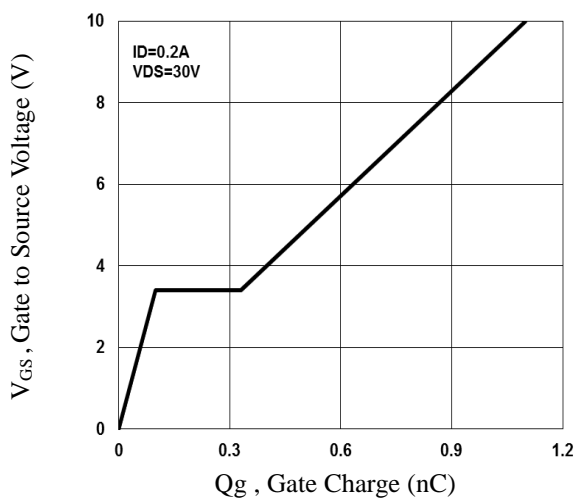
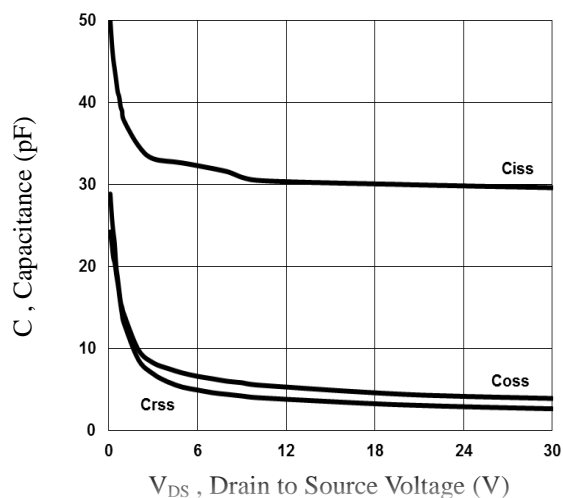
Q _g	Total Gate Charge ^{2, 3}	V _{DS} =30V, V _{GS} =10V, I _D =0.2A	---	1.1	2	nC
Q _{gs}	Gate-Source Charge ^{2, 3}		---	0.1	0.2	
Q _{gd}	Gate-Drain Charge ^{2, 3}		---	0.23	0.5	
T _{d(on)}	Turn-On Delay Time ^{2, 3}	V _{DD} =30V, V _{GS} =10V, R _G =6Ω I _D =0.2A	---	3	6	ns
T _r	Rise Time ^{2, 3}		---	5	10	
T _{d(off)}	Turn-Off Delay Time ^{2, 3}		---	14	27	
T _f	Fall Time ^{2, 3}		---	9	17	
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, F=1MHz	---	30.6	45	pF
C _{oss}	Output Capacitance		---	5.5	10	
C _{rss}	Reverse Transfer Capacitance		---	4	8	

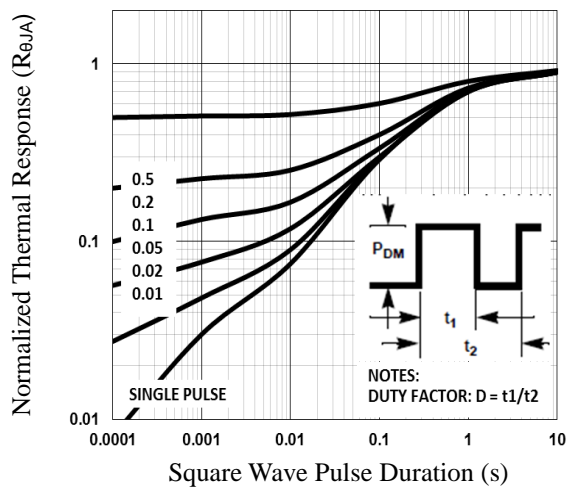
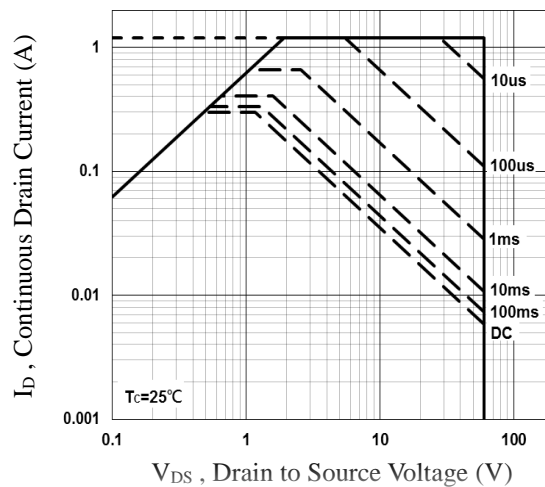
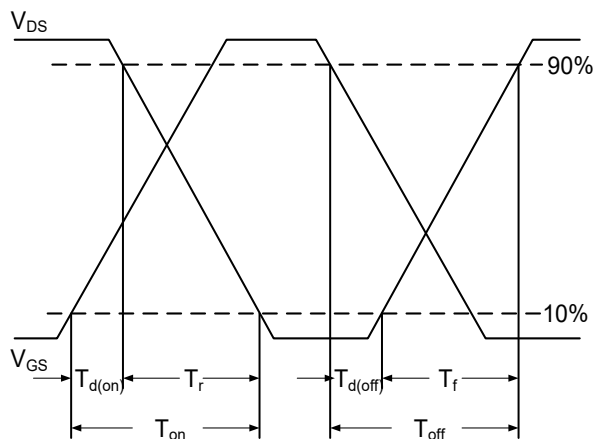
Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	0.3	A
I _{SM}	Pulsed Source Current		---	---	0.6	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.4	V

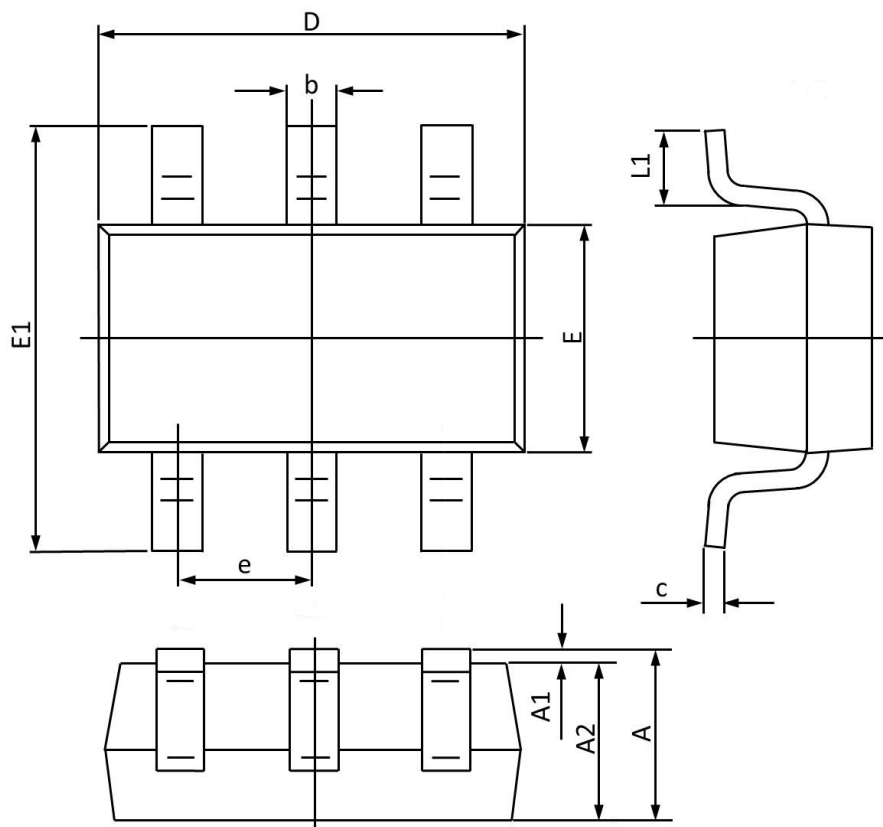
Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.


Fig.1 Output Characteristics

Fig.2 Continuous Drain Current vs. T_J

Fig.3 Normalized $R_{DS(on)}$ vs. T_J

Fig.4 Normalized V_{th} vs. T_J

Fig.5 Gate Charge Waveform

Fig.6 Capacitance Characteristics


Fig.7 Normalized Transient Impedance

Fig.8 Maximum Safe Operation Area

Fig.9 Switching Time Waveform

SOT363 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
A1	0.100	0.000	0.004	0.000
A2	1.000	0.800	0.039	0.031
b	0.330	0.100	0.013	0.004
c	0.250	0.100	0.010	0.004
D	2.200	1.800	0.087	0.071
E	1.350	1.150	0.053	0.045
E1	2.400	1.800	0.094	0.071
e	0.65BSC		0.026BSC	
L1	0.350	0.100	0.014	0.004

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